

\ line 23, change "trench" to --the trench--.

Page 9, line 3, after "215." insert --The source region 220 is isolated from the

insulation film 216. ~~add~~

\ line 25, change "is less than" to --is equal to or less than--.

IN THE DRAWINGS:

Fig. 11B is amended as shown in red in the marked sheet attached to the Request for Approval of Drawing Correction.

IN THE CLAIMS:

\ Please cancel claims 11 and 13 without prejudice or disclaimer.

\ Please amend claims 1, 7, 9, 10, 12 and 14 as follows:

1. (Amended) A bipolar semiconductor device comprising:
  - a drain electrode;
  - a drain region having a first conductive type and disposed on the drain electrode;
  - a drift region having a second conductive type different from the first conductive type and disposed on the drain region;
  - a channel region having the second conductive type and disposed on the drift region;
  - a gate region provided so as to surround at least a part of the channel region via an insulation film;
  - a source region having the second conductive type provided on the channel region, the source region is located substantially at a center of the channel region, and the source region is isolated from the insulation film; and

A<sup>2</sup> consid.  
C<sup>1</sup> word

a source electrode connected to the source region.

Claim 7, \ line 2, change "semiconductor" to --semiconductor layer--; and

\ line 3, change "thereof" to --of the semiconductor layer--.

Claim 9, \ line 4, change "space" to --distance--.

Claim 10, \ line 2, change "conductive" to --semiconductor--; and

\ line 4, change "space" to --distance--.

12. (Amended) A semiconductor device comprising:

a substrate having a first conductive type;

a drift region having the first conductive type and disposed on the substrate;

a channel region having a second conductive type different from the first

conductive type and provided on the drift region;

a gate region provided so as to surround the channel region; and

a source region having the [second] first conductive type and provided on the

channel region, the source region is located substantially at a center of the channel region, and

9 wherein the source region is isolated from [the insulation film] wherein:

an impurity concentration of the channel region is equal to or less than an

112 1st impurity concentration in the drift region, and [a depletion layer forms over the entire channel

region sandwiched between the gate region when a zero bias is applied to the gate region.]

14. (Amended) A semiconductor device comprising:

a cathode region having a first conductive type;

a channel region disposed on the <sup>cathode</sup> [channel] region, the channel region having a

second conductive type different from the first conductive type;

<sup>upper portion of A<sup>3</sup>B</sup> an anode region disposed on the channel region, wherein:

sub  
B1  
A3

figs. 9B, 10B

112 1st

A4 3  
fig 11B

A4  
esid. p. 9  
11/21/01

[an impurity concentration in the channel region is equal to or less than an impurity concentration in the cathode region]

Please add new claims 16-19 as follow:

--16. A bipolar semiconductor device, comprising:

- a drain electrode;
- a drain region having a first conductive type and disposed on the drain electrode;
- a drift region having a second conductive type different from the first conductive type and disposed on the drain region;
- a channel region having the second conductive type and disposed on the drift region;
- a gate region provided so as to surround at least a part of the channel region via an insulation film;
- a source region having the second conductive type provided on the channel region;
- a source electrode connected to the source region; and
- a semiconductor layer having the second conductive type, located between the source region and the source electrode, and an end face of the semiconductor layer is extended to a position covering at least a portion of the gate region.--

--17. The semiconductor device according to claim 16, wherein a thickness of an insulating film formed on an upper portion of the gate region is thicker than a thickness of an insulating film formed on a side portion of the gate region.--

--18. The semiconductor device according to claim 16, further comprising an insulating film located between the semiconductor layer and the source electrode and having